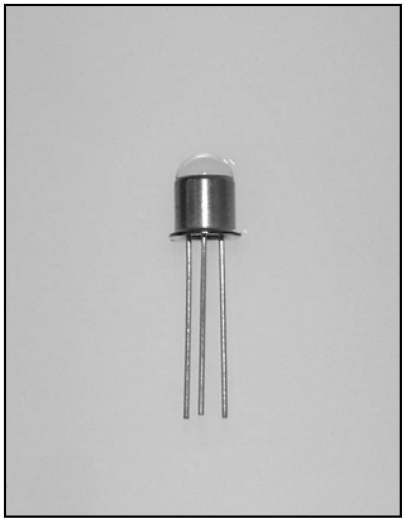
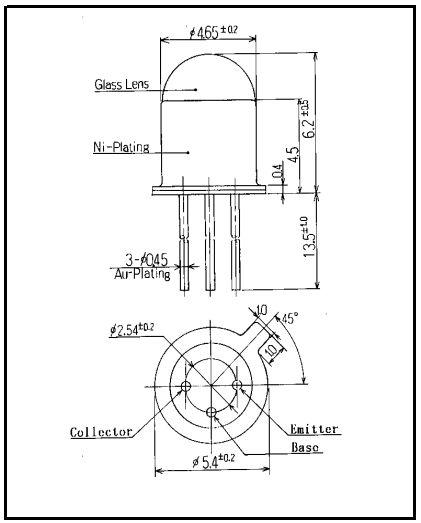
PT086N4

Photo Transistor





Dimensions (Unit:mm)

FEATURES
- High Reliability

APPLICATIONS
- Optical Switches
- Optical Sensors
- Edge Sensing
- Smoke Detectors

1. ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

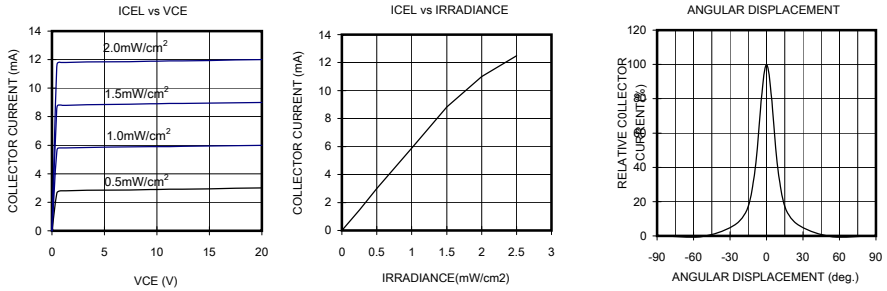
I T E M	SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage	Vceo	30	V
Collector-Base Voltage	Vcbo	30	V
Emitter-Base Voltage	Vebo	5	V
Emitter-Collector Voltage	Veco	5	V
Collector Current	Ic	50	mA
Collector Power Dissipation	Pc	250	mW
Operating Temp.	Topr	-30 TO 100	℃
Storage Temp.	Tstg	-40 TO 125	℃
Junction Temp.	Tj	125	℃
Lead Soldering Temp.*	Tls	260	℃

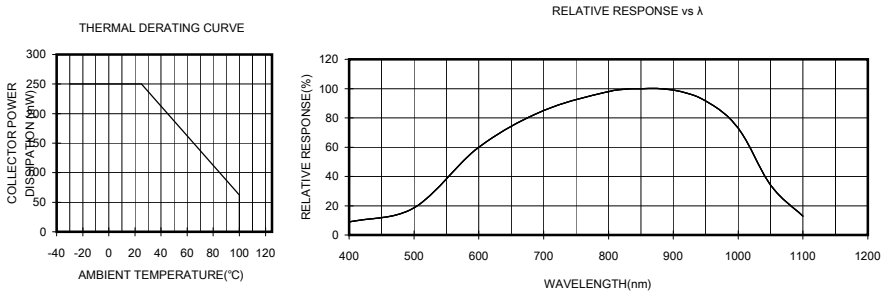
*Time 5 Sec max,Position:Up to 3mm from the body

2.ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25℃)

I T E M	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Collector Emitter Current	Icel	Vce=20V,Ee=0.5mw/cm^2※		3.0		mA
Collector Dark Current	Iceo	Vce=20V,Ee=0mw/cm^2※			100	nA
C-E Saturation Voltage	VCE(sat)	Ic=0.2mA,Ee=5mw/cm^2※		0.2		V
Spectral sensitivity	λ			400 ~ 1100		nm
Peak Sensitivity Wave Length	λp			880		nm
Switching time (Rise Time)	Tr	RL=100Ω,Vce=5V,Ic=0.5mA		10.0		μS
Switching time (Fall Time)	Tf	RL=100Ω,Vce=5V,Ic=0.5mA		10.0		μS
Angular Response	θ			±12		deg

※ Color Temperature=2870°K Standard Tungsten Lump





To purchase this part contact
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lead-free RoHS